MOSFETs Silicon N-Channel MOS (DTMOS II)

TK20E60U

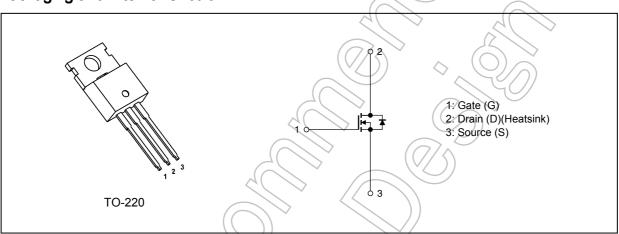
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.165 \Omega$ (typ.)
- (2) High forward transfer admittance: $|\,Y_{\rm fs}\,|$ = 12 S (typ.)
- (3) Low leakage current: I_{DSS} = 100 μ A (max) (V_{DS} = 600 V)
- (4) Enhancement mode: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage	(// 5)	V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	20	A
Drain current (pulsed)	(Note 1)	I _{DP}	40	
Power dissipation (T _c = 25	(C)	PD	190	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	144	mJ
Avalanche current	(Note 3)	I _{AR}	10	A
Repetitive avalanche energy	(Note 3)	E _{AR}	19	mJ
Reverse drain current (DC)	(Note 1)	I _{DR}	20	A
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	40	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.658	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 2.52 mH, R_G = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

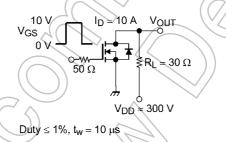
6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	—	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	\bigvee		100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600		—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	$\left \left \right\rangle \right $	5.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 10 A	7	0.165	0.19	Ω
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	3	12	_	S

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	1470	$\overline{\langle}$	pF
Reverse transfer capacitance	C _{rss}		- (150	I	
Output capacitance	C _{oss}		((3500	_	
Switching time (rise time)	tr	See Figure 6.2.1	X	40) —	ns
Switching time (turn-on time)	t _{on}		\sim	80	_	
Switching time (fall time)	t _f			12	—	
Switching time (turn-off time)	t _{off}		~ 1	100	_	





6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	—	27	—	nC
Gate-source charge	Q _{gs}	\sim	_	16	_	
Gate-drain charge	Qgd		_	11	—	

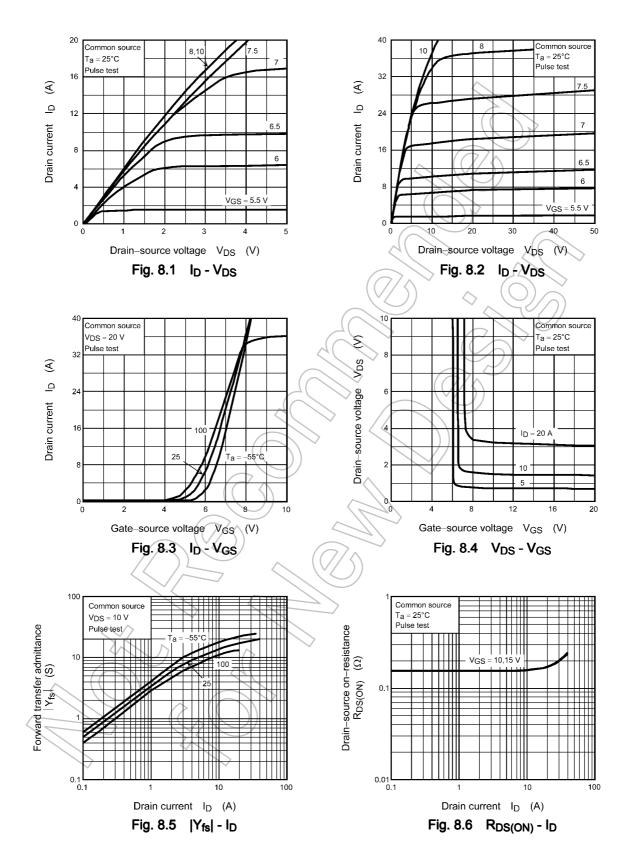
6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

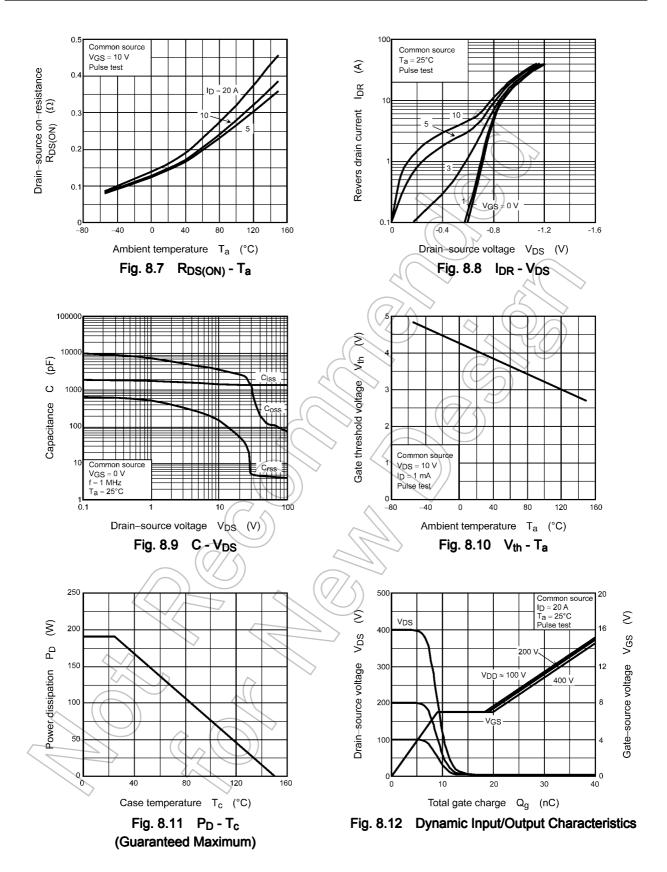
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I_{DR} = 20 A, V_{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		$I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V}$	_	450	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	8.1	_	μC

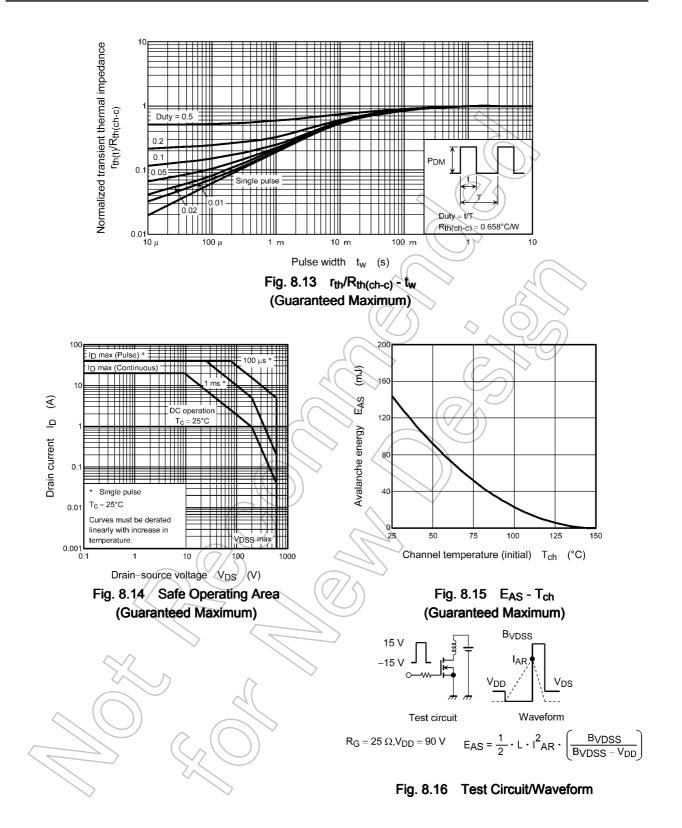
7. Marking



8. Characteristics Curves (Note)





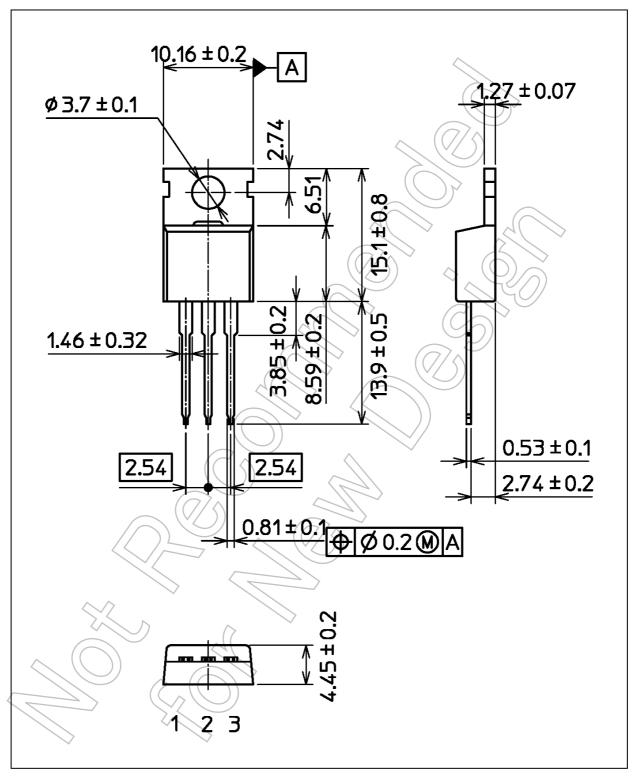


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm

TK20E60U





	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	

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